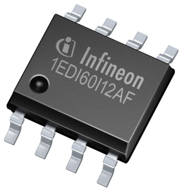
EiceDRIVER™ 1EDI Compact 150 mil

Datasheet

1EDIxxI12AF, 1EDIxxN12AF, and 1EDIxxI12MF
EiceDRIVER™ 1EDI Compact Single channel multi-purpose gate driver IC



✓ RoHS

Green

Features

- Single channel isolated gate driver
- For 600 V/650 V/1200 V IGBTs, MOSFETs and SiC MOSFETs
- Up to 10 A typical peak current at rail-to-rail outputs
- Separate source and sink outputs (AF variants) or combined output with Miller clamp (MF variants)
- Galvanically isolated coreless transformer driver
- Wide input voltage operating range
- Suitable for operation at high ambient temperature and in fast switching applications
- High common-mode transient immunity *CMTI* > 100 kV/s
- Small and cost optimized DSO-8 150 mil package with 4 mm creepage
- 40 V absolute maximum output supply voltage (AF variants)

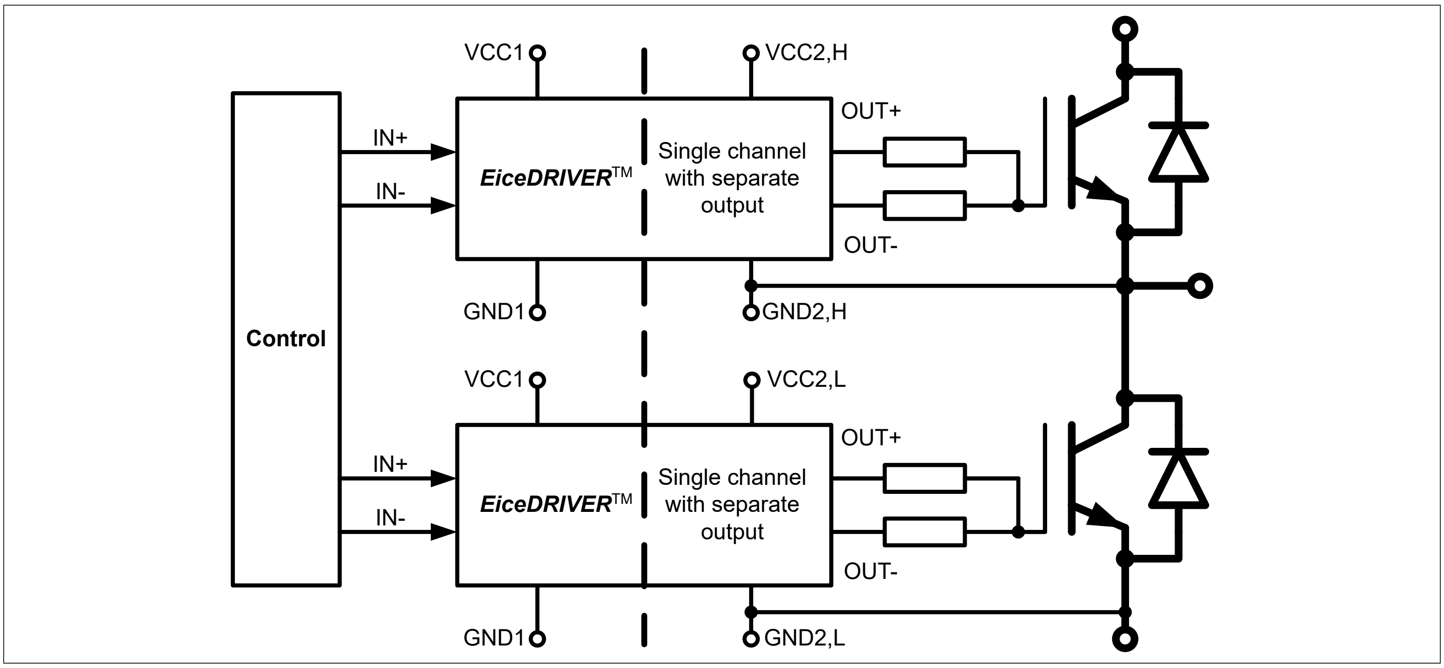
Potential applications

- AC and brushless DC motor drives
- High voltage DC/DC-converter and DC/AC-inverter
- Induction heating resonant application
- UPS-systems
- Commercial air-conditioning (CAC)
- Server and telecom switched mode power supplies (SMPS)
- Solar

Product validation

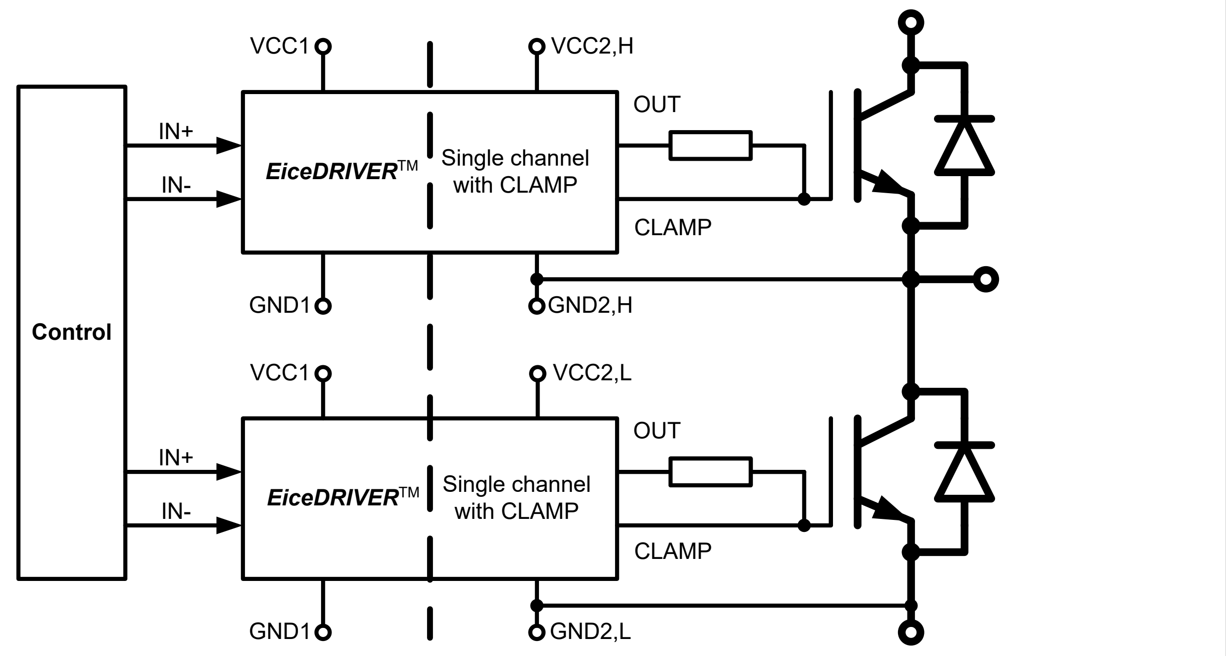
Qualified for industrial applications according to the relevant tests of JEDEC JESD47, JESD22, and J-STD-020.

Description



Typical application 1EDIxxI12AF and 1EDIxxN12AF

The EiceDRIVER™ Compact 1EDIxxI12AF and 1EDIxxN12AF are galvanically isolated single channel gate driver in a DSO-8 narrow body package that provide output currents up to 10 A at separated output pins.



Typical application 1EDIxxI12MF

The EiceDRIVER™ Compact 1EDIxxI12MF are galvanically isolated single channel gate driver in a DSO-8 narrow body package that provide output currents up to 6.2 A and an integrated active Miller clamp circuit with the same current rating to protect against parasitic turn on.

The input logic pins operate on a wide input voltage range from 3 V to 15 V using scaled CMOS threshold levels to support even 3.3 V microcontrollers.
Every driver family member comes with logic input and driver output undervoltage lockout (UVLO) and active shutdown.

Product type	Typical output current and configuration	UVLO	VCC2 (max)	Propagation delay	Package marking
1EDI20I12AF	4.0 A source and sink outputs	12 V	40 V	300 ns	1I20I12A
1EDI20N12AF	4.0 A source and sink outputs	9.1 V	40 V	120 ns	1I20N12A
1EDI40I12AF	7.5 A source and sink outputs	12 V	40 V	300 ns	1I40I12A
1EDI60I12AF	10.0 A source and sink outputs	12 V	40 V	300 ns	1I60I12A
1EDI60N12AF	10.0 A source and sink outputs	9.1 V	40 V	120 ns	1I60N12A
1EDI20I12MF	4.4 A with 2.0 A Miller clamp	12 V	20 V	300 ns	1I20I12M
1EDI30I12MF	6.2 A with 3.0 A Miller clamp	12 V	20 V	300 ns	1I30I12M

Table of contents

1 Block diagram reference

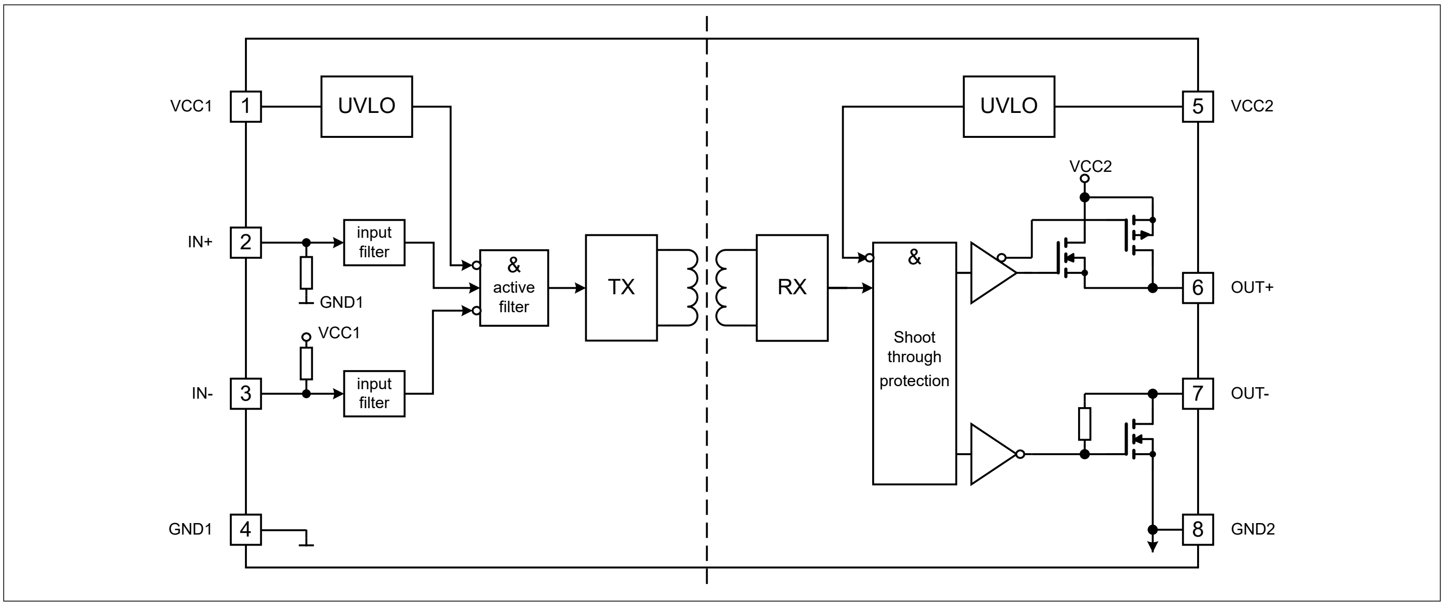


Figure 3 **Block diagram 1EDIxxI12AF and 1EDIxxN12AF**

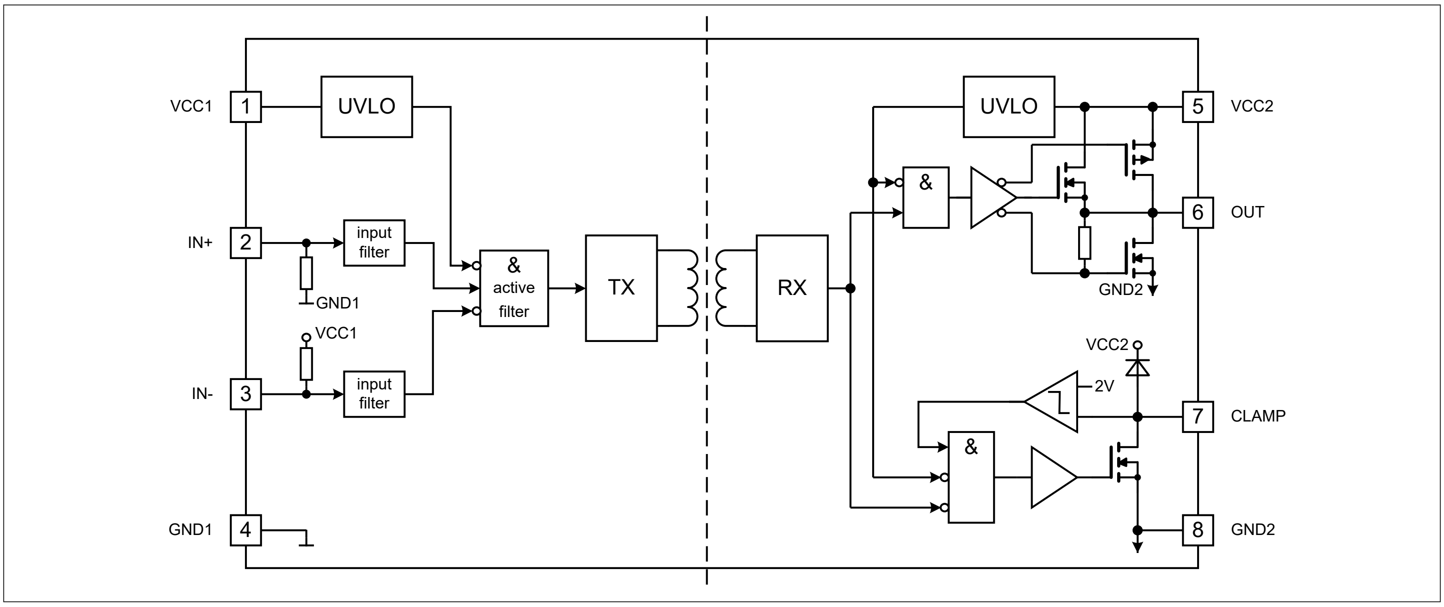


Figure 4 **Block diagram 1EDIxxI12MF**

2 Pin configuration and functionality

Pin configuration 1EDIxxI12AF and 1EDIxxN12AF

Table 1 **Pin configuration**

Pin No.	Name	Function
1	*VCC1*	Positive logic supply
2	*IN+*	Non-inverted driver input (active high)
3	*IN-*	Inverted driver input (active low)
4	*GND1*	Logic ground
5	*VCC2*	Positive power supply output side
6	*OUT+*	Driver source output
7	*OUT-*	Driver sink output
8	*GND2*	Power ground

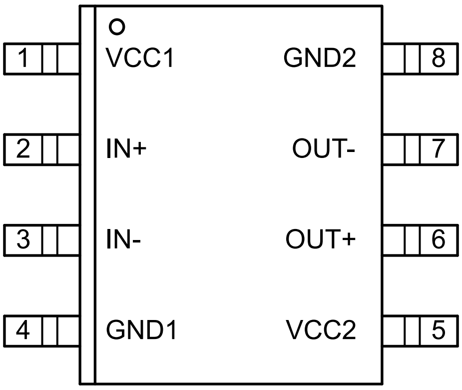


Figure 5 **DSO-8 narrow body (top view)**

Pin configuration 1EDIxxI12MF

Table 2 **Pin configuration**

Pin No.	Name	Function
1	*VCC1*	Positive logic supply
2	*IN+*	Non-inverted driver input (active high)
3	*IN-*	Inverted driver input (active low)
4	*GND1*	Logic ground
5	*VCC2*	Positive power supply voltage
6	*OUT*	Driver output
7	*CLAMP*	Active Miller clamp
8	*GND2*	Power ground

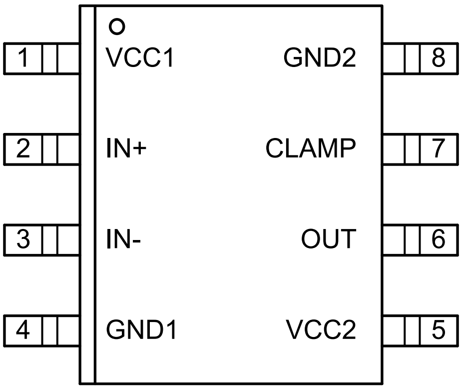


Figure 6 **DSO-8 narrow body (top view)**

Pin functionality

Pin name	Functionality
VCC1	Logic input supply voltage of 3.3 V up to 15 V wide operating range.
IN+	*IN+* non-inverted control signal for driver output if *IN-* is set to low. (Output sourcing active at *IN+* = high and *IN-* = low) Due to internal filtering a minimum pulse width is defined to ensure robustness against noise at *IN+*. An internal weak pull-down-resistor favors off-state.
IN-	*IN-* inverted control signal for driver output if *IN+* is set to high. (Output sourcing active at *IN-* = low and *IN+* = high) Due to internal filtering a minimum pulse width is defined to ensure robustness against noise at *IN-*. An internal weak pull-up-resistor favors off-state.
GND1	Ground connection of input circuit.
VCC2	Positive power supply pin of output driving circuit. A proper blocking capacitor has to be placed close to this supply pin.
OUT+	1EDIxxI12AF and 1EDIxxN12AF: Driver source output pin to turn on external IGBT. During on-state the driving output is switched to *VCC2*. Switching of this output is controlled by *IN+* and *IN-*. This output will also be turned off at an UVLO event. During turn off the *OUT+* terminal is able to sink approx. 100 mA. In case of an unconnected *OUT-* the complete gate charge is discharged through this channel resulting in a slow turn off.
OUT-	1EDIxxI12AF and 1EDIxxN12AF: Driver sink output pin to turn off external IGBT. During off-state the driving output is switched to *GND2*. Switching of this output is controlled by *IN+* and *IN-*. In case of UVLO an active shut down keeps the output voltage at a low level.
OUT	1EDIxxI12MF: Combined source and sink output pin to external IGBT. The output voltage will be switched between *VCC2* and *GND2* and is controlled by *IN+* and *IN-*. In case of an UVLO event this output will be switched off and an active shut down keeps the output voltage at a low level.
CLAMP	1EDIxxI12MF: Connect gate of external IGBT directly to this pin. As soon as the gate voltage has dropped below 2 V referred to *GND2* during turn off state the Miller clamp function ties its output to *GND2* to avoid parasitic turn on of the connected IGBT.
GND2	Reference ground of the output driving circuit.

3 Functional description

The 1EDIxxI12AF, 1EDIxxN12AF, and 1EDIxxI12MF are general purpose isolated gate drivers. Basic control and protection features support fast and easy design of highly reliable systems.

The integrated galvanic isolation between control input logic and driving output stage grants additional safety. Its wide input voltage supply range supports the direct connection of various signal sources like DSPs and microcontrollers.

The separated rail-to-rail driver outputs of 1EDIxxI12AF and 1EDIxxN12AF simplify gate resistor selection, save an external high current bypass diode and enhance dV/dt control.

1EDIxxI12MF also provides the rail-to-rail output and the additional active Miller clamp to suppress dynamic turn on due to Miller capacitance.

3.1 Supply

The driver can operate over a wide supply voltage range, either unipolar or bipolar depending on maximum output voltage of the individual variant.

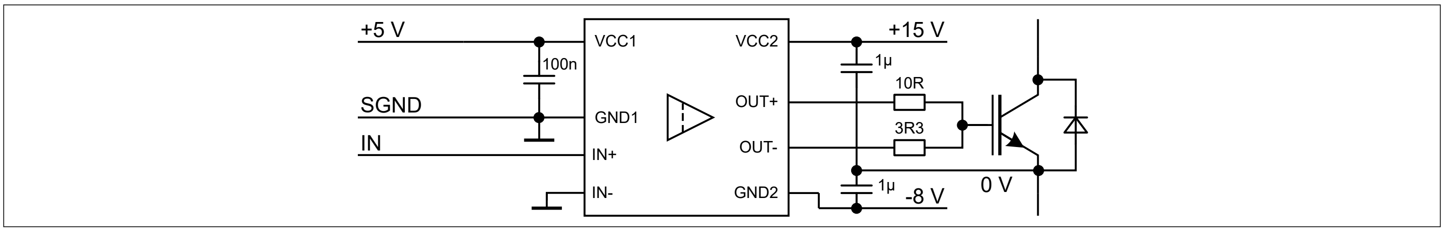


Figure 7 Application example bipolar supply with separate outputs

With bipolar supply the driver is typically operated with a positive voltage of 15 V at *VCC2* and a negative voltage of -8 V at *GND2* relative to the emitter of the IGBT. Negative supply can help to prevent a dynamic turn on due to the additional charge which is generated from IGBT's input capacitance.

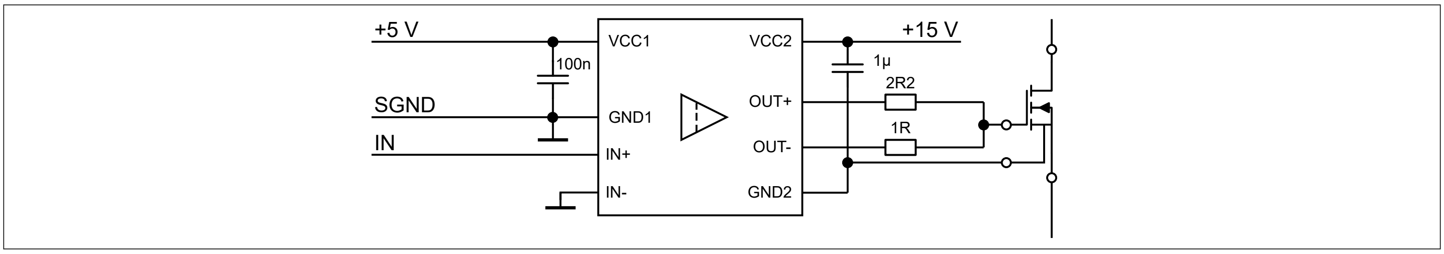


Figure 8 Application example unipolar supply with separate outputs

For unipolar supply configuration the driver is typically supplied with a positive voltage of 15 V at *VCC2*. In this case, careful evaluation for turn off gate resistor selection is recommended to avoid dynamic turn on.

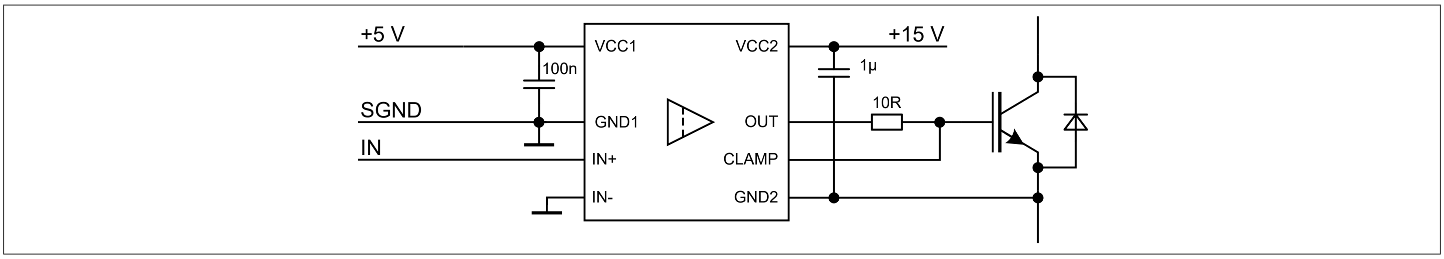


Figure 9 Application example unipolar supply with Miller clamp

The typical positive supply voltage for the driver is 15 V at *VCC2*. Erratical dynamic turn on of the IGBT can be prevented with the active Miller clamp function, in which the *CLAMP* output is directly connected to the IGBT gate.

3.2 Protection features

3.2.1 Undervoltage lockout (UVLO)

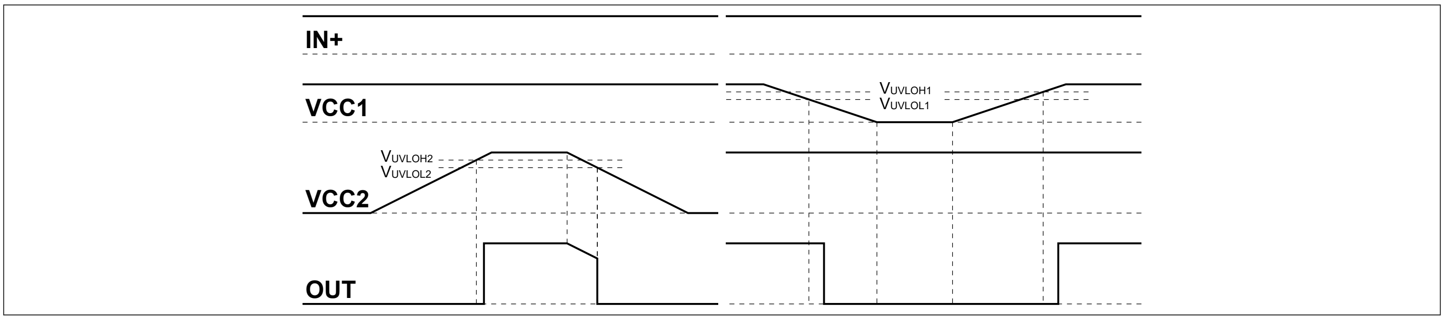


Figure 10 UVLO behavior

To ensure correct switching of IGBTs the device is equipped with an undervoltage lockout for input and output independently. Operation starts only after both VCC levels have increased beyond the respective V_{UVLOH} levels.

If the power supply voltage V_{VCC1} of the input chip drops below V_{UVLOL1} a turn-off signal is sent to the output chip before power-down. The IGBT is switched off and the signals at *IN+* and *IN-* are ignored until V_{VCC1} reaches the power-up voltage V_{UVLOH1} again.

If the power supply voltage V_{VCC2} of the output chip goes down below V_{UVLOL2} the IGBT is switched off and signals from the input chip are ignored until V_{VCC2} reaches the power-up voltage V_{UVLOH2} again.

***Note**: V_{VCC2} is always referred to GND2 and does not differentiate between unipolar or bipolar supply.*

3.2.2 Active shutdown

The active shut-down feature ensures a safe IGBT off-state in case the output chip is not connected to the power supply or an undervoltage lockout is in effect.

For 1EDIxxI12AF and 1EDIxxN12AF, the IGBT gate is clamped at *OUT-* to *GND2*.

For 1EDIxxI12MF, the IGBT gate is clamped at *CLAMP* to *GND2*.

3.2.3 Short circuit clamping

During short circuit the IGBTs gate voltage tends to rise because of the feedback via the Miller capacitance. An internal protection circuit limits this voltage to a value slightly higher than the supply voltage.

For 1EDIxxI12AF and 1EDIxxN12AF, the IGBT gate is clamped at *OUT+* to *VCC2*.

For 1EDIxxI12MF, the IGBT gate is clamped at *CLAMP* to *VCC2*.

A maximum current of 500 mA may be fed back to the supply through this path for 10 µs. If higher currents are expected or tighter clamping is desired external Schottky diodes may be added.

3.2.4 Active Miller clamp

The active Miller clamp function is only implemented in the 1EDIxxI12MF variants.

In a half bridge configuration the switched off IGBT tends to dynamically turn on during turn on phase of the opposite IGBT. A Miller clamp allows sinking the Miller current across a low impedance path in this high dV/dt situation. Therefore in many applications, the use of a negative supply voltage can be avoided. During turn-off, the gate voltage is monitored and the clamp output is activated when the gate voltage drops below typical 2 V (referred to *GND2*). The clamp is designed for a Miller current in the same range as the nominal output current.

3.3 Non-inverting and inverting inputs

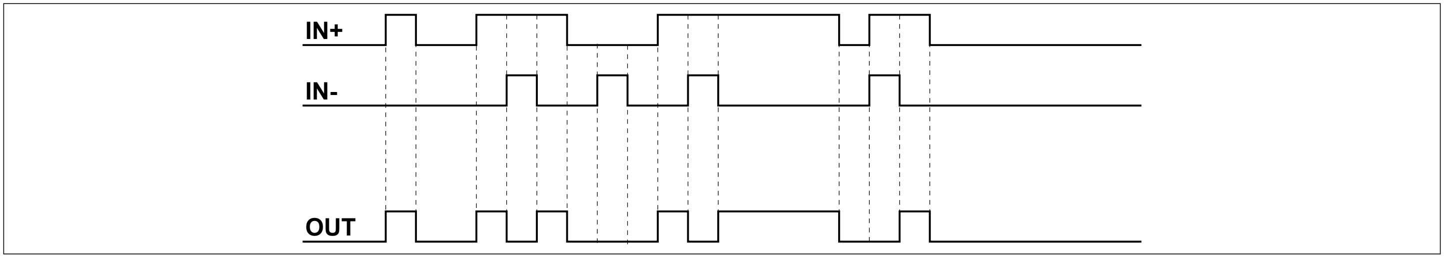


Figure 11 **Logic input to output switching behavior**

There are two possible input modes to control the IGBT. At non-inverting mode *IN+* controls the driver output while *IN-* is set to low. At inverting mode *IN-* controls the driver output while *IN+* is set to high. A minimum input pulse width is defined to filter occasional glitches.

3.4 Driver outputs

The output driver section uses MOSFETs to provide a rail-to-rail output. This feature permits that tight control of gate voltage during on-state and short circuit can be maintained as long as the driver's supply is stable. Due to the low internal voltage drop, switching behavior of the IGBT is predominantly governed by the gate resistor. Furthermore, it reduces the power to be dissipated by the driver.

4 Electrical characteristics and parameters

4.1 Absolute maximum ratings

Note: *Absolute maximum ratings are defined as ratings, which when being exceeded may lead to destruction of the integrated circuit. Unless otherwise noted all parameters refer to GND1.*

Table 3 Absolute maximum ratings

Parameter	Symbol	Values		Unit	Note or test condition
		Min.	Max.		
Power supply output side (1EDIxxI12AF and 1EDIxxN12AF)	V_{VCC2}	-0.3	40	V	1)
Power supply output side (1EDIxxI12MF)	V_{VCC2}	-0.3	20 2)	V	1)
Gate driver output	V_{OUT}	V_{GND2}-0.3	V_{VCC2}+0.3	V	1)
Positive power supply input side	V_{VCC1}	-0.3	18.0	V	–
Logic input voltages (*IN+*,*IN-*)	$V_{LogicIN}$	-0.3	18.0	V	–
Input to output isolation voltage (*GND2*)	V_{GND2}	-1200	1200	V	*GND2 - GND1*
Junction temperature	T_J	-40	150	°C	–
Storage temperature	T_S	-55	150	°C	–
Comparative tracking index	*CTI*	600	–		IEC 60664-1: Material group I
Power dissipation (Input side)	$P_{D, IN}$	–	25	mW	3) @T_A = 25°C
Power dissipation (Output side)	$P_{D, OUT}$	–	400	mW	3) @T_A = 25°C
Thermal resistance (Input side)	$R_{THJA,IN}$	–	145	K/W	3) @T_A = 85°C
Thermal resistance (Output side)	$R_{THJA,OUT}$	–	165	K/W	3) @T_A = 85°C
ESD capability	$V_{ESD,HBM}$	–	2	kV	Human body model 4)
	$V_{ESD,CDM}$	–	1	kV	Charged device model 5)

1) With respect to *GND2*.
2) May be exceeded during short circuit clamping.
3) See Figure 15 for reference layouts for these thermal data. Thermal performance may change significantly with layout and heat dissipation of components in close proximity.
4) According to ANSI/ESDA/JEDEC-JS-001-2017 (discharging a 100 pF capacitor through a 1.5 kΩ series resistor).
5) According to ANSI/ESDA/JEDEC-JS-002-2014 (TC = test condition in volt)

4.2 Operating parameters

Note: *Within the operating range the IC operates as described in the functional description. Unless otherwise noted all parameters refer to GND1.*

Table 4 Operating parameters

Parameter	Symbol	Values		Unit	Note or test condition
		Min.	Max.		
Power supply output side (1EDIxxI12AF and 1EDIxxN12AF)	V_{VCC2}	13	35	V	(1)
Power supply output side (1EDIxxI12MF)	V_{VCC2}	13	18	V	(1)
Power supply input side	V_{VCC1}	3.1	17	V	–
Logic input voltages (*IN+*,*IN-*)	V_{LogicIN}	-0.3	17	V	–
Switching frequency	f_{sw}	–	1.0	MHz	(2) (3)
Ambient temperature	T_{A}	-40	125	°C	–
Thermal coefficient, junction-top	$\Psi_{\mathrm{th,jt}}$	–	4.8	K/W	(3) at T_{A} = 85°C
Common mode transient immunity (CMTI)	$\lvert dV_{\mathrm{ISO}}/dt\rvert$	–	100	kV/µs	(3) at 1000 V

1) With respect to *GND2*.
2) do not exceed maximum power dissipation
3) Parameter is not subject to production test - verified by design/characterization

4.3 Electrical characteristics

Note: *The electrical characteristics include the spread of values in supply voltages, load and junction temperatures given below. Typical values represent the median values at T_A = 25°C. Unless otherwise noted all voltages are given with respect to their respective GND (GND1 for pins 1 to 3, GND2 for pins 5 to 7).*

4.3.1 Voltage supply

Table 5 Voltage supply

Parameter	Symbol	Values			Unit	Note or test condition
		Min.	Typ.	Max.		
UVLO threshold input chip	V_{UVLOH1}	–	2.85	3.1	V	–
	V_{UVLOL1}	2.55	2.75	–	V	–
UVLO hysteresis input chip (V_{UVLOH1} - V_{UVLOL1})	V_{HYS1}	0.09	0.10	–	V	–
UVLO threshold output chip (1EDIxxI12AF and 1EDIxxI12MF)	$V_{UVLOH2,1}$	–	12.0	12.7	V	[1]
	$V_{UVLOL2,1}$	10.5	11.1	–	V	[1]
UVLO hysteresis output chip ($V_{UVLOH2,1}$ - $V_{UVLOL2,1}$)	$V_{HYS2,1}$	0.70	0.85	–	V	–
UVLO threshold output chip (1EDIxxN12AF)	$V_{UVLOH2,2}$	–	9.1	10.0	V	[1]
	$V_{UVLOL2,2}$	8.0	8.5	–	V	[1]
UVLO hysteresis output chip ($V_{UVLOH2,2}$ - $V_{UVLOL2,2}$)	$V_{HYS2,2}$	0.55	0.60	–	V	–
Quiescent current input chip	I_{Q1}	–	0.65	1.0	mA	V_{VCC1} = 5 V *IN+* = High, *IN-* = Low =>*OUT* = High
Quiescent current output chip	I_{Q2}	–	1.2	2.0	mA	V_{VCC2} = 15 V *IN+* = High, *IN-* = Low =>*OUT* = High

[1] With respect to *GND2*.

4.3.2 Logic input

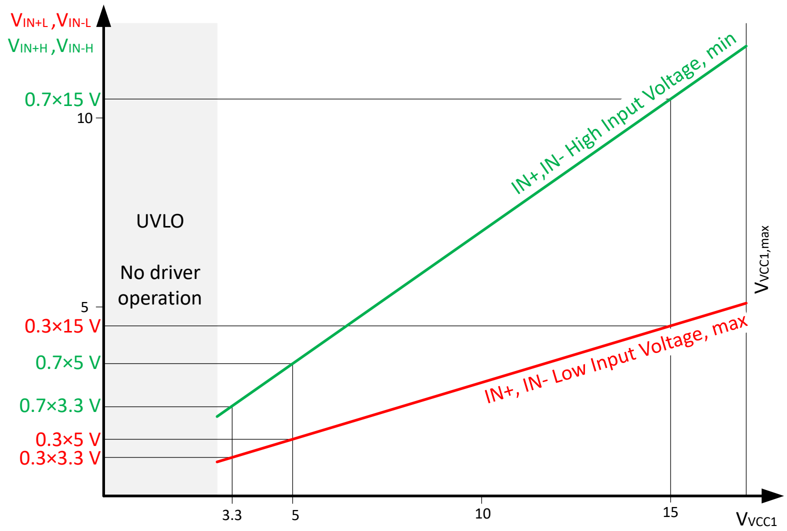


Figure 12 ***VCC1* scaled input threshold voltage of *IN+* and *IN-***

Beginning from the input undervoltage lockout level, threshold levels for *IN+* and *IN-* are scaled to V_{VCC1}. The high input threshold is 70% of V_{VCC1} and the low input threshold is at 30% of V_{VCC1}.

Table 6 **Logic input**

Parameter	Symbol	Values			Unit	Note or test condition
		Min.	Typ.	Max.		
IN+,*IN-* low input voltage	V_{IN+L}, V_{IN-L}	–	–	0.3 × V_{VCC1}		[1] 3.1 V ≤ V_{VCC1} ≤ 17 V
IN+,*IN-* high input voltage	V_{IN+H}, V_{IN-H}	0.7 × V_{VCC1}	–	–		
IN+,*IN-* low input voltage	V_{IN+L}, V_{IN-L}	–	–	1.5	V	V_{VCC1} = 5.0 V
IN+,*IN-* high input voltage	V_{IN+H}, V_{IN-H}	3.5	–	–	V	
IN- input current	I_{IN-}	–	70	200	µA	V_{VCC1} = 5.0 V, V_{IN-} = *GND1*
IN+ input current	I_{IN+}	–	70	200	µA	V_{VCC1} = 5.0 V, V_{IN+} = V_{VCC1}

1) Parameter is not subject to production test - verified by design/characterization

4.3.3 Gate driver

***Note**: minimum Peak current rating valid over temperature range!*

Table 7 Gate driver

Parameter	Symbol	Values			Unit	Note or test condition
		Min.	Typ.	Max.		
High level output peak current (source) 1EDI20I12AF, 1EDI20N12AF 1EDI40I12AF 1EDI60I12AF, 1EDI60N12AF	$I_{OUT+,PEAK}$	 2.0 4.0 6.0	 4.0 7.5 10.0	–	A	[1] [2] $IN+$ = High, $IN-$ = Low, V_{VCC2} = 15 V
Low level output peak current (sink) 1EDI20I12AF, 1EDI20N12AF 1EDI40I12AF 1EDI60I12AF, 1EDI60N12AF	$I_{OUT-,PEAK}$	 2.0 4.0 6.0	 3.5 6.8 9.4	–	A	[1] [2] $IN+$ = Low, $IN-$ = Low, V_{VCC2} = 15 V
High level output peak current (source) 1EDI20I12MF 1EDI30I12MF	$I_{OUT,H,PEAK}$	 2.0 3.0	 4.4 5.9	–	A	[3] [2] $IN+$ = High, $IN-$ = Low, V_{VCC2} = 15 V
Low level output peak current (sink) 1EDI20I12MF 1EDI30I12MF	$I_{OUT,L,PEAK}$	 2.0 3.0	 4.1 6.2	–	A	[3] [2] $IN+$ = Low, $IN-$ = Low, V_{VCC2} = 15 V

[1] specified min. output current is forced; voltage across the device $V_{(VCC2 - OUT+)}$ or $V_{(OUT- - GND2)} < V_{VCC2}$.

[2] Parameter is not subject to production test - verified by design/characterization

[3] specified min. output current is forced; voltage across the device $V_{(VCC2 - OUT)}$ or $V_{(OUT - GND2)} < V_{VCC2}$.

4.3.4 Short circuit clamping

Table 8 Short circuit clamping (1EDIxxI12AF and 1EDIxxN12AF)

Parameter	Symbol	Values			Unit	Note or Test Condition
		Min.	Typ.	Max.		
Clamping voltage (*OUT+*) ($V_{\text{OUT+}}$ - V_{VCC2})	V_{CLPout}	–	0.9	1.3	V	1) *IN+* = High, *IN-* = Low, *OUT* = High I_{OUT} = 500 mA, (pulse test t_{CLPmax} = 10 µs)

1) With respect to *GND2*.

Table 9 Short circuit clamping (1EDIxxI12MF)

Parameter	Symbol	Values			Unit	Note or Test Condition
		Min.	Typ.	Max.		
Clamping voltage (*OUT*) (V_{OUT} - V_{VCC2})	V_{CLPout}	–	0.9	1.3	V	1) *IN+* = High, *IN-* = Low, I_{OUT} = 500 mA (pulse test t_{CLPmax} = 10 µs)
Clamping voltage (*CLAMP*) (V_{VCLAMP} - V_{VCC2})	$V_{\text{CLPclamp1}}$	–	1.3	–	V	1) *IN+* = High, *IN-* = Low, I_{CLAMP} = 500 mA (pulse test t_{CLPmax} = 10 µs)
Clamping voltage (*CLAMP*)	$V_{\text{CLPclamp2}}$	–	0.7	1.1	V	1) *IN+* = High, *IN-* = Low, I_{CLAMP} = 20 mA

1) With respect to *GND2*.

4.3.5 Active Miller clamp

Table 10 Active Miller clamp (1EDIxxI12MF only)

Parameter	Symbol	Values			Unit	Note or Test Condition
		Min.	Typ.	Max.		
Low level clamp current 1EDI20I12MF 1EDI30I12MF	$I_{\text{CLAMP,PEAK}}$	 2.0 3.0	–	–	A	1) *IN+* = Low, *IN-* = Low, V_{CLAMP} = 15 V pulsed t_{pulse} = 2 µs
Clamp threshold voltage	V_{CLAMP}	1.6	2.0	2.4	V	2)

1) Parameter is not subject to production test - verified by design/characterization
2) With respect to *GND2*.

4.3.6 Dynamic characteristics

Dynamic characteristics are measured with V_{VCC1} = 5 V and V_{VCC2} = 15 V.

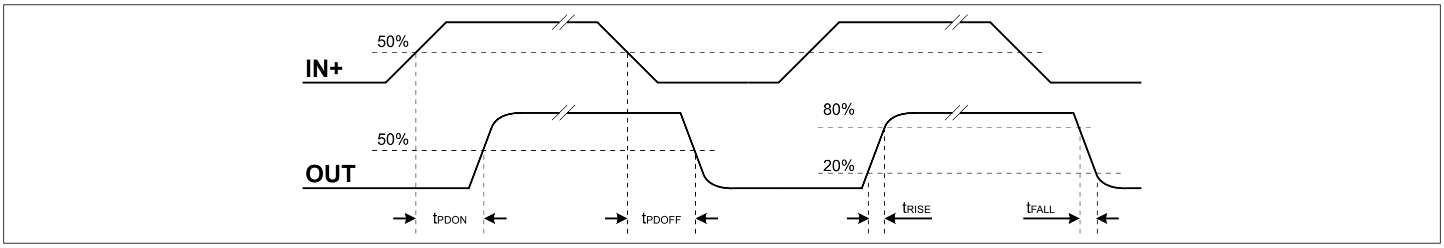


Figure 13 Propagation delay, rise and fall time

Table 11 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note or Test Condition
		Min.	Typ.	Max.		
Input IN to output propagation delay ON	t_{PDON}	270	300	330	ns	C_{LOAD} = 100 pF V_{IN+} = 50%, V_{OUT}=50% @25°C 1EDIxxI12AF, 1EDIxxI12MF
Input IN to output propagation delay OFF	t_{PDOFF}	270	300	330	ns	
Input IN to output propagation delay distortion (t_{PDOFF} - t_{PDON})	t_{PDISTO}	-30	5	40	ns	
Input pulse suppression time *IN*+, *IN*-	t_{MININ+}, t_{MININ-}	230	240	–	ns	
Input IN to output propagation delay ON	t_{PDON}	95	120	142	ns	C_{LOAD} = 100 pF V_{IN+} = 50%, V_{OUT}=50% @25°C 1EDIxxN12AF
Input IN to output propagation delay OFF	t_{PDOFF}	105	125	150	ns	
Input IN to output propagation delay distortion (t_{PDOFF} - t_{PDON})	t_{PDISTO}	-15	5	25	ns	
Input pulse suppression time *IN*+, *IN*-	t_{MININ+}, t_{MININ-}	30	40	–	ns	
Input IN to output propagation delay ON variation due to temp	t_{PDONt}	–	–	14	ns	1) C_{LOAD} = 100 pF V_{IN+} = 50%, V_{OUT}=50%
Input IN to output propagation delay OFF variation due to temp	t_{PDOFFt}	–	–	14	ns	
Input IN to output propagation delay distortion variation due to temp (t_{PDOFF}-t_{PDON})	$t_{PDISTOt}$	–	–	8	ns	
Rise time	t_{RISE}	–	10	20	ns	C_{LOAD} = 1 nF V_L 20%, V_H 80%
Fall time	t_{FALL}	–	9	19	ns	

1) Parameter is not subject to production test - verified by design/characterization

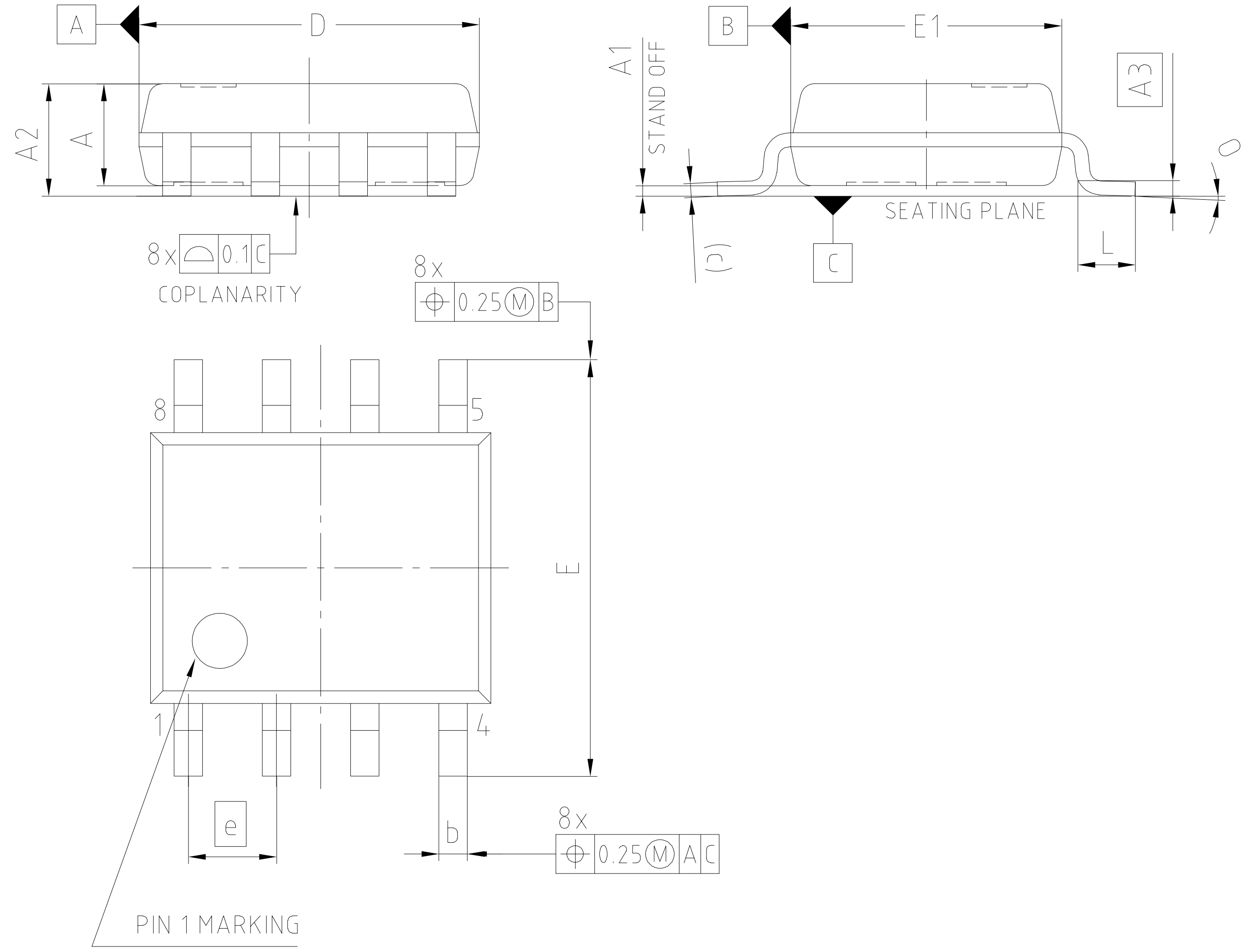
4.3.7 Active shutdown

Table 12 Active shut down

Parameter	Symbol	Values			Unit	Note or Test Condition
		Min.	Typ.	Max.		
Active shut down voltage	V_{ACTSD}	–	2.2	2.5	V	(1) $I_{\mathrm{OUT,L}}/I_{\mathrm{OUT,L,PEAK}}$=0.1, *VCC2* open

(1) With respect to *GND2*.

5 Package dimensions



PACKAGE - GROUP NUMBER:	PG-DSO-8-U05	
DIMENSIONS	**MILLIMETERS**	
	MIN.	MAX.
A	1.25	1.47
A1	0.10	0.25
A2	---	1.72
A3	0.25	
b	0.35	0.49
c	0.20	
D	4.80	5.00
E	5.80	6.20
E1	3.80	4.00
e	1.27	
L	0.41	1.27
O	---	8°

NOTES: DIMENSIONS DO NOT INCLUDE MOLD FLASH, PROTRUSION OR GATE BURRS

Figure 14 DSO-8 narrow body (Plastic (green) dual small outline package)

6 Application notes

6.1 Reference layout for thermal data

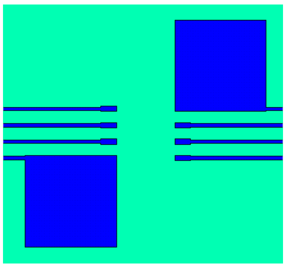


Figure 15 Reference layout for thermal data (Copper thickness 35 µm)

This PCB layout represents the reference layout used for the thermal characterization.

Pin 4 (GND1) and pin 8 (GND2) require each a ground plane of 100 mm^2 for achieving maximum power dissipation. The package is built to dissipate most of the heat generated through these pins.

The thermal coefficient junction-top ($\Psi_{\mathrm{th,jt}}$) can be used to calculate the junction temperature at a given top case temperature and driver power dissipation:

$$T_j = \Psi_{\mathrm{th,jt}} \cdot P_D + T_{\mathrm{top}}$$

6.2 Printed circuit board guidelines

The following factors should be taken into account for an optimum PCB layout.

- Sufficient spacing should be kept between high voltage isolated side and low voltage side circuits.
- The same minimum distance between two adjacent high-side isolated parts of the PCB should be maintained to increase the effective isolation and to reduce parasitic coupling.
- In order to ensure low supply ripple and clean switching signals, bypass capacitor trace lengths should be kept as short as possible.

Revision history

Document version	Date of release	Description of changes
1.20	2025-12-16	• Change of template and merging of datasheets (1EDI-AF and 1EDI-MF) into a single family datasheet • Update of package outline drawing • Editorial changes
1.10	2023-06-23	• Change of template and version numbering system • formatting updated for electrical parameters and pins, separate output variant data sheets merged • minimum value of t_{RISE} and t_{FALL} removed • Added footnote for gate driver output current

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